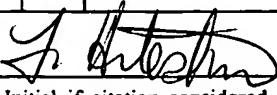
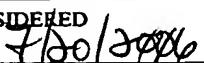


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Sheet 1 of 1

Form PTO-1449 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE			ATTY DOCKET NO. 122336		APPLICATION NO. New U.S. National Stage of PCT/JP03/08671	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)						
			APPLICANTS Ryoji HOSHI et al.			
			FILING DATE January 4, 2005			
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
FH.	1.	US 2002/0000189 A1	01/03/2002	Tadami TANAKA et al.		
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
FH.	2.	JP-A-2000-044389 w/ abst. & trans.	02/15/2000	JAPAN		
↑	3.	JP-A-2001-151596 w/ abst. & trans.	06/05/2001	JAPAN		
	4.	JP-A-2000-219598 w/ abst. & trans.	08/08/2000	JAPAN		
	5.	WO 01/27362 A1 w/ abst.	04/19/2001	JAPAN		
	6.	JP-A-2001-274167 w/ abst. & trans.	10/05/2001	JAPAN		
	7.	JP-A-2002-012499 w/ abst. & trans.	01/15/2002	JAPAN		
↓	8.	JP-A-2000-109396 w/ abst. & trans.	04/18/2000	JAPAN		
FH.	9.	JP-A-2002-076007 w/ abst. & trans.	03/15/2002	JAPAN		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
FH.	10.	Talid SINNO et al.; "Modeling Microdefect Formation in Czochralski Silicon"; <i>Journal of the Electrochemical Society</i> ; 146 (6); 1999; pp. 2300-2312.				
EXAMINER 					DATE CONSIDERED 	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						